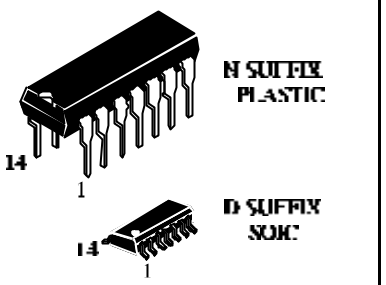
Quad 2-Input NAND Gate with Open-Drain Outputs

High-Performance Silicon-Gate CMOS



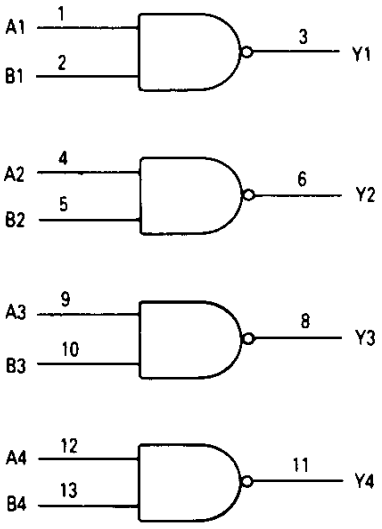
ORDERING INFORMATION
SL74HC03N Plastic
SL74HC03D SOIC
T_A = -55° to 125° C for all packages

The SL74HC03 is identical in pinout to the LS/ALS03. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

The SL74HC03 NAND gate has, as its output, a high-performance MOS N-Channel transistor. This NAND gate can, therefore, with a suitable pullup resistor, be used in wired-AND applications.

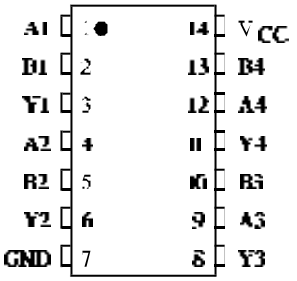
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices

LOGIC DIAGRAM



PIN 14 =V_{CC}
PIN 7 = GND

PIN ASSIGNMENT



FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z= High Impedance

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{IN}	DC Input Voltage (Referenced to GND)	-1.5 to V_{CC} +1.5	V
V_{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} +0.5	V
I_{IN}	DC Input Current, per Pin	±20	mA
I_{OUT}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
Tstg	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		-55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	V_{CC} =2.0 V V_{CC} =4.5 V V_{CC} =6.0 V	0 0 0	1000 500 400	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND≤(V_{IN} or V_{OUT})≤V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

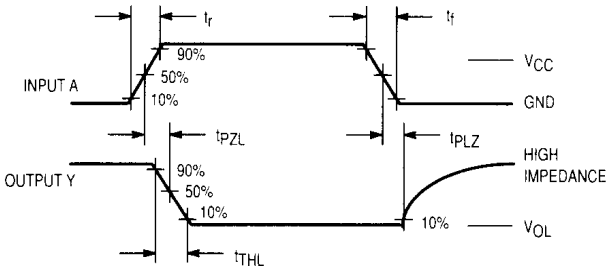
DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V_{IH}	Minimum High-Level Input Voltage	V_{OUT}=0.1 V or V_{CC}-0.1 V $\|I_{OUT}\| \le 20\ \mu A$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low -Level Input Voltage	V_{OUT}=0.1 V or V_{CC}-0.1 V $\|I_{OUT}\| \le 20\ \mu A$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
V_{OL}	Maximum Low-Level Output Voltage	V_{IN}=V_{IH} $\|I_{OUT}\| \le 20\ \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V_{IN}=V_{IH} $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA	 4.5 6.0	 0.26 0.26	 0.33 0.33	 0.4 0.4	
I_{IN}	Maximum Input Leakage Current	V_{IN}=V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{IN}=V_{CC} or GND I_{OUT}=0μA	6.0	1.0	10	40	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V_{IN}= V_{IL} or V_{IH} I_{OUT}= V_{CC} or GND	6.0	±0.5	±5.0	±10	μA

AC ELECTRICAL CHARACTERISTICS(C_L=50pF,Input t_r=t_f=6.0 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit 25 °C to -55°C	Guaranteed Limit ≤85°C	Guaranteed Limit ≤125°C	Unit
t_{PLZ}, t_{PZL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 4.5 6.0	120 24 20	150 30 26	180 36 31	ns
t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{IN}	Maximum Input Capacitance	-	10	10	10	pF
C_{OUT}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	10	10	10	pF

C_{PD}	Power Dissipation Capacitance (Per Gate) Used to determine the no-load dynamic power consumption: $P_D=C_{PD}V_{CC}^2f+I_{CC}V_{CC}$	Typical @25°C,V_{CC}=5.0 V 8.0	pF



.Figure 1. Switching Waveforms

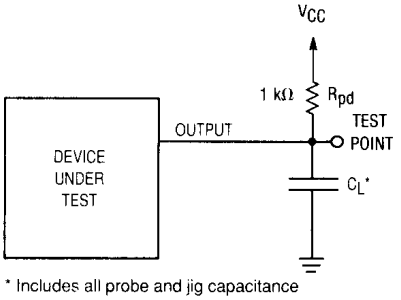
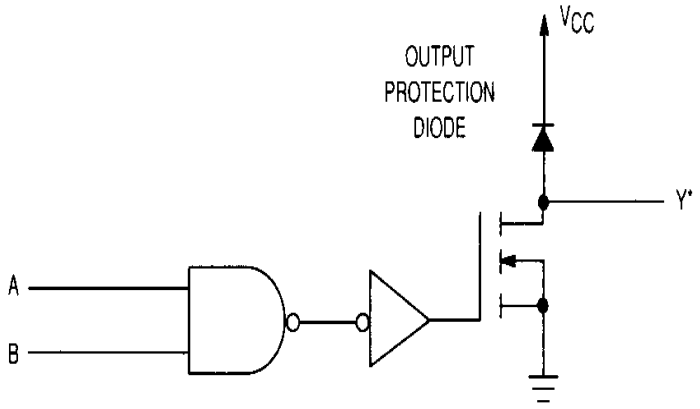


Figure 2. Test Circuit

EXPANDED LOGIC DIAGRAM
(1/4 of the Device)



* Denotes open-drain outputs